

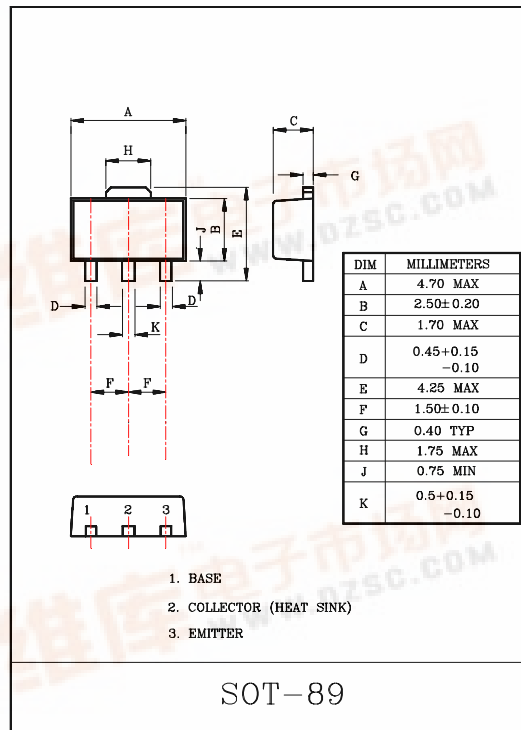
HIGH CURRENT APPLICATION.

FEATURES

- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTA1664.

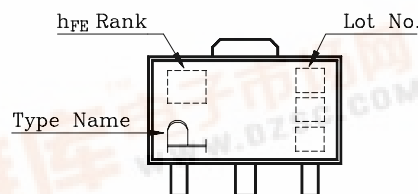
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	35	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	800	mA
Base Current	I _B	160	mA
Collector Power Dissipation	P _C	500	mW
	P _{C*}	1	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



P_{C*} : KTC4376 mounted on ceramic substrate (250mm²x0.8t)

Marking



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} =35V, I _E =0	-	-	100	nA
Emitter-Cut-off Current	I _{EBO}	V _{EB} =5V, I _C =0	-	-	100	nA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	30	-	-	V
DC Current Gain	h _{FE} (1) (Note)	V _{CE} =1V, I _C =100mA	100	-	320	
	h _{FE} (2)	V _{CE} =1V, I _C =700mA	35	-	-	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =500mA, I _B =20mA	-	-	0.5	V
Base-Emitter Voltage	V _{BE}	V _{CE} =1V, I _C =10mA	0.5	-	0.8	V
Transition Frequency	f _T	V _{CE} =5V, I _C =10mA	-	120	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz	-	13	-	pF

Note : h_{FE} Classification O:100~200, Y:160~320



KTC4376

